

## List of Figures

Figures	Title	Page
1.1	Applications of flexible organic electronics; <b>(a)</b> a flexible seven segment display (Image source: electroiq.com). <b>(b)</b> An ultra-thin and wearable LED display (Image source: www.independent.co.uk). <b>(c)</b> A flexible color e-reader display with OTFT back plane (Image source: Plastic logic). <b>(d)</b> An ultra-flexible organic circuitry (Image source: www.printedelectronicworld.com). <b>(e)</b> A wearable flexible AMOLED display (Image source: Plastic logic).	2
1.2	Chemical structure of various organic semiconductors; <b>(a)</b> C8-BTBT. <b>(b)</b> Sexithiophene. <b>(c)</b> MEH-PPV. <b>(d)</b> TIPS-pentacene. <b>(e)</b> Anthracene. <b>(f)</b> Pentacene. <b>(g)</b> DNNT. <b>(h)</b> P <sub>3</sub> HT. <b>(i)</b> Tetracene. <b>(j)</b> PPV. <b>(k)</b> Rubrene. <b>(l)</b> PTAA. <b>(m)</b> CuPC. <b>(n)</b> PQT-12.	3
1.3	Classification of organic semiconductors.	3
1.4	General chemical structure of small molecule <b>(a)</b> , and polymeric <b>(b)</b> organic semiconductors.	4
1.5	<b>(a)</b> sp <sup>2</sup> hybridized orbitals in carbon atom. <b>(b)</b> Orbital level interactions in a small unit in a $\pi$ conjugated molecule. <b>(c)</b> Canonical structures of benzene molecule. <b>(d)</b> Interactions in molecular orbitals of benzene and subsequent delocalization of $\pi$ electrons.	4
1.6	<b>(a)</b> Linear combination of two p <sub>x</sub> and two p <sub>z</sub> atomic orbitals to form bonding ( $\sigma$ and $\pi$ ) and antibonding ( $\sigma^*$ and $\pi^*$ ) molecular orbitals respectively. <b>(b)</b> Linear combination of many p <sub>z</sub> orbitals to form energy bands.	6
1.7	Some common solution processing techniques; <b>(a)</b> Drop casting. <b>(b)</b> Spin coating. <b>(c)</b> Dip coating. <b>(d)</b> Inkjet printing. <b>(e)</b> Screen printing. <b>(f)</b> Blade coating.	8
1.8	OFET device architectures; <b>(a)</b> Bottom gate top contact. <b>(b)</b> Top gate bottom contact. <b>(c)</b> Bottom gate bottom contact. <b>(d)</b> Top gate bottom contact.	9
1.9	Metal-semiconductor energy band diagram for p-type <b>(a)</b> , and n-type <b>(b)</b> organic semiconductors.	10
1.10	Operating principle of an OFET in linear mode <b>(a)</b> , onset of saturation <b>(b)</b> , and saturation mode <b>(c)</b> .	10
1.11	Various factors affecting performance of devices.	11
2.1	<b>(a)</b> A complete cycle in the atomic layer deposition process. <b>(b)</b> Savannah S-200 ALD system from Cambridge nanotech used in experiments.	17
2.2	<b>(a)</b> Complete process of film formation in spin coating method. <b>(b)</b> WS-650 MHz-BNPP/LITE spin coating system from Laurell used in experiments.	18
2.3	<b>(a)</b> Drop casting procedure and crystal formation. <b>(b)</b> Actual drop casting on a silicon sample. <b>(c)</b> Optical micrograph of obtained crystals.	19
2.4	<b>(a)</b> Material deposition in thermal evaporation method. <b>(b)</b> SC-Triaxis thermal evaporation system from Semicore used in experiments.	20
2.5	<b>(a)</b> Linear surface profile measurement from stylus based profilo-meter. <b>(b)</b> DektakXT surface profilo-meter system from Bruker used in measurements.	21
2.6	<b>(a)</b> Simplified principle of X-ray diffraction measurements. <b>(b)</b> D8-advanced X-ray diffraction measurement system from Bruker used in analysis.	22
2.7	<b>(a)</b> Simplified working principle of atomic force microscopy technique. <b>(b)</b> XE-70 surface probe microscopy system from Park Systems used in surface characterization.	23
2.8	<b>(a)</b> Simplified working principle of scanning electron microscopy. <b>(b)</b> EVO-18 special edition scanning electron microscope from Carl Zeiss used in characterization.	24
2.9	<b>(a)</b> Simplified working principle of UV-visible absorbance spectroscopy. <b>(b)</b> UV-1800 UV-visible spectrophotometer from Shimadzu used in characterization.	24
2.10	<b>(a)</b> 4200-SCS Semiconductor parameter analyzer from Keithley used in electrical characterization. <b>(b)</b> PM-5 probe station from Cascade Microtech used for housing and probing sample during electrical characterization.	25
2.11	A transfer <b>(a)</b> , and output <b>(b)</b> characteristics of a specimen OFET, showing various electrical parameters of the device.	26
3.1	A representation of the solubility analysis on Teas graph. Dashed line represents solubility-window of TIPS-pentacene. Various solvents and binary solvent mixtures have been indicated on the graph as H (hexane), C (cyclohexane), B (benzene), T (toluene), T:B (toluene\benzene), T:C (toluene\cyclohexane), and T:H (toluene/hexane).	29

3.2	A Schematic representation of TIPS-pentacene solution formation. Solute-solute, solvent-solvent, and solute-solvent intermolecular forces are represented by solid, double-lined and dotted arrows respectively. Height of the arrow indicates relative strength of the force. Arrow pointing down indicates attractive forces whereas a down pointing arrow signifies repulsive forces among molecules. <b>(a)</b> TIPS-pentacene and toluene in an unmixed state. <b>(b)</b> TIPS-pentacene and toluene just mixed with each other. <b>(c)</b> Solution is formed with very strong interactions between TIPS-pentacene. <b>(d)</b> A solution in the presence of hexane (non-solvent). The presence of non-solvent molecules causes a lesser repulsive force among TIPS-pentacene molecules.	31
3.3	Molecular structures of various solvents; toluene <b>(a)</b> , benzene <b>(b)</b> , cyclohexane <b>(c)</b> , and hexane <b>(d)</b> . <b>(e)</b> The solvent evaporation behavior of TIPS-pentacene drop cast solution. <b>(f)</b> Device structure of a bottom-gate top-contact TIPS-pentacene OFET.	32
3.4	Optical micrographs and surface morphologies of TIPS-pentacene crystals obtained by solutions of toluene <b>(a) &amp; (e)</b> , toluene/benzene <b>(b) &amp; (f)</b> , toluene/cyclohexane <b>(c) &amp; (g)</b> , and toluene/hexane <b>(d) &amp; (h)</b> . Similar surface morphologies of the crystals in the image <b>(e)</b> and <b>(f)</b> confirm similar behavior of the toluene and toluene/benzene solutions. As the dissimilarity between the additive and the main solvent rises, more irregularities in the terracing structure can be observed.	33
3.5	X-ray diffractograms for TIPS-pentacene crystals obtained from several solutions. An additive solvent with higher dissimilarity has the least ability to surmount the intermolecular forces between TIPS-pentacene molecules, which causes a higher degree of crystallinity.	33
3.6	Output and transfer characteristics of OFETs obtained from solutions of toluene <b>(a) &amp; (b)</b> ; toluene/benzene <b>(c) &amp; (d)</b> ; toluene/cyclohexane <b>(e) &amp; (f)</b> and toluene/hexane <b>(g) &amp; (h)</b> .	35
3.7	Variation in the field-effect mobility and integrated intensity values for OFETs fabricated using various solvents.	36
4.1	Device structure of neat TIPS-pentacene OFETs with SiO <sub>2</sub> dielectric <b>(a)</b> , and TIPS-pentacene:PS blend OFETs <b>(b)</b> .	39
4.2	Optical micrograph of a crystal obtained from solutions of neat TIPS-pentacene on SiO <sub>2</sub> substrate <b>(a)</b> , and TIPS-pentacene:PS blend on SiO <sub>2</sub> substrate <b>(b)</b> .	40
4.3	Cross sectional SEM image for neat TIPS-pentacene film <b>(a)</b> , and TIPS-pentacene:PS blend film <b>(b)</b> . Fig. 4.3 (b) shows a clear phase separation in TIPS-pentacene:polymer blend structure.	40
4.4	AFM image of a crystal obtained from solutions of neat TIPS-pentacene <b>(a)</b> , and TIPS-pentacene:PS blend <b>(b)</b> . <b>(c)</b> X-ray diffractogram of neat TIPS-pentacene and TIPS-pentacene:PS blend film indicating higher crystallinity in the blend films.	41
4.5	<b>(a) &amp; (b)</b> Output and <b>(c) &amp; (d)</b> transfer characteristics of a representative neat TIPS-pentacene and TIPS-pentacene:PS blend OFET respectively.	42
4.6	Drain current decay as a function of stress time. Total stress time was 2 h and current values were recorded in the interval of 30 s.	44
4.7	Recovery from the effects of bias stress in the saturation regime for a neat TIPS-pentacene device with SiO <sub>2</sub> <b>(a)</b> , and TIPS-pentacene:PS blend device <b>(b)</b> .	45
4.8	Repeatability of electrical characteristics for a neat TIPS-pentacene device with SiO <sub>2</sub> <b>(a)</b> , and TIPS-pentacene:PS blend device <b>(b)</b> . TIPS-pentacene:PS device demonstrates a well consistent performance with nearly unchanged performance parameters.	46
5.1	Device structure of flexible top contact neat TIPS-pentacene OFET <b>(a)</b> , and TIPS-pentacene:PS blend OFETs <b>(b)</b> .	48
5.2	<b>(a)</b> Digital image of fabricated devices. Optical micrographs of semiconductor crystal obtained from neat TIPS-pentacene solution <b>(b)</b> , and TIPS-pentacene:PS blend solution <b>(c)</b> .	49
5.3	Optical micrographs of TIPS-pentacene:PS blend crystals before etching <b>(a)</b> , and after etching from n-hexane <b>(b)</b> .	49
5.4	Surface morphology of HfO <sub>2</sub> <b>(a)</b> , cross linked PVP <b>(b)</b> , crystal obtained from the neat TIPS-pentacene solution <b>(c)</b> , and TIPS-pentacene:PS blend solution <b>(d)</b> .	50
5.5	X-ray diffratograms for TIPS-Pentacene crystals obtained from neat TIPS-pentacene and TIPS-pentacene:PS blend solutions.	50
5.6	Output and transfer characteristics for a representative neat TIPS-pentacene <b>(a)</b> , <b>(b)</b> and TIPS-pentacene:PS blend OFET <b>(c)</b> , <b>(d)</b> .	51
5.7	Bias stress induced decay in normalized drain current in TIPS-pentacene OFETs as a function of stress time at V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -10 V.	53
6.1	Strategy for application of tensile strain <b>(a)</b> , and multiple cycles of tensile and compressive	56

	strain <b>(b)</b> . A single cycle of strain application follows I.→II.→III.→IV.→I.	
6.2	<b>(a)</b> AFM image of the TIPS-pentacene crystal obtained from the PS blend solution. <b>(b)</b> Optical micrograph of a TIPS-pentacene crystal revealing a distinct PS rich layer under the TIPS-pentacene crystal. <b>(c)</b> Line profile along the solid line in the optical micrograph. Thicknesses of the PS rich layer and TIPS-pentacene crystal were found to be $140 \pm 20$ nm and $416 \pm 88$ nm respectively.	57
6.3	Output <b>(a)</b> and transfer <b>(b)</b> characteristics of a representative TIPS-pentacene:PS blend flexible OFET.	58
6.4	<b>(a)</b> Transfer characteristics of a representative device for strain duration varying from un-bent to 2 days. <b>(b)</b> Variation in mobility and threshold voltage with strain duration.	58
6.5	Transfer characteristics of device on logarithmic scale <b>(a)</b> , and linear scale <b>(b)</b> after undergoing multiple cycles of mechanical stress at $R_{\text{bend}}$ of $\pm 5$ mm for a $t_{\text{bend}}$ of 5 s.	59
6.6	<b>(a)</b> Bias-stress induced decay in normalized drain current for various device conditions. <b>(b)</b> Shift in threshold voltage with stress time.	59
7.1	Electronic transitions in an organic semiconductor. Photon absorption (1); Photo-induced absorption (7); Radiative transitions: fluorescence (2), Phosphorescence (6); Intersystem crossing (4); Non-radiative transitions (3, 5); CP state generation by branching (8); CP <sub>L</sub> state generation by relaxation and vibrational energy (9→10).	65
7.2	UV and visible absorption spectrum of TIPS-pentacene.	67
7.3	Transfer characteristics of TIPS-pentacene OFET on linear and logarithmic scales respectively for blue <b>(a) &amp; (b)</b> , green <b>(c) &amp; (d)</b> , and red illumination <b>(e) &amp; (f)</b> , with varying intensity.	68
7.4	Variation in current modulation <b>(a)</b> , and photo-responsivity <b>(b)</b> , with applied gate voltage for various illuminations.	69
7.5	<b>(a)</b> Effect of illumination time with constant biasing conditions ( $V_{\text{GS,bias}} = 10$ V, $V_{\text{DS,bias}} = 0$ V) on the photo-response. <b>(b)</b> Exponential variation of $V_{\text{TH}}$ with illumination time. <b>(c)</b> Dependence of maximum current modulation and photoresponsivity on illumination time.	70
7.6	<b>(a)</b> Effect of gate bias during illumination on the photo-response of an OFET for constant illumination time of 100 s. <b>(b)</b> Linear dependence of shift in $V_{\text{TH}}$ on the applied gate bias during illumination. <b>(c)</b> Variation of maximum current modulation and photo-responsivity with the applied gate bias during illumination.	71
7.7	<b>(a)</b> Dynamic response of TIPS-pentacene photo-OFET for different illuminations. <b>(b)</b> Illustration of drain current response for a single cycle of blue light illumination. Trapping and release rates were extracted from the initial 30 s of the ON and OFF regions.	72
7.8	Transfer characteristics of TIPS-pentacene OFET on logarithmic <b>(a)</b> , and linear scales <b>(b)</b> , under UV irradiation.	75
7.9	<b>(a)</b> Effect of UV illumination time on the transfer characteristics of the OFET. <b>(b)</b> Variation of $\mu_{\text{sat}}$ and $V_{\text{TH}}$ with increasing illumination time. <b>(c)</b> Trend of maximum drain current at $V_{\text{GS}} = -10$ V with increasing illumination time. <b>(d)</b> X-ray diffractogram of a pristine and 10 minute UV irradiated sample.	76
7.10	<b>(a)</b> Effect of increasing gate bias during illumination on the transfer characteristics of an OFET for a constant illumination time of 100 s. <b>(b)</b> Dependence of $\mu_{\text{sat}}$ and shift in $V_{\text{TH}}$ on the applied gate bias during illumination.	77
7.11	<b>(a)</b> UV switching response of TIPS-pentacene OFETs. <b>(b)</b> Variation in $(I_{\text{DS}}(t))^{1/2}$ for a single cycle of UV illumination. Slopes have been extracted from the linear fit in the ON and OFF regions.	78